

forming said concave portion, and a side of said portion of said lower electrode layer, a side of said ferroelectric layer and a side of said upper electrode layer are flush with each other.

2. (Amended) A ferroelectric memory, comprising:

an insulation film having a hollow at a top surface; and

a laminated body obtained by laminating a plurality of layers on said top surface and etching a region of said plurality of layers corresponding to a region other than said hollow, wherein said laminated body includes a lower electrode layer, a ferroelectric layer formed on said lower electrode layer and an upper electrode layer formed on said ferroelectric layer; and the memory further comprising a film formed in a bottom of said hollow and separating between said insulation film and said lower electrode layer.

3. (Twice Amended) A ferroelectric memory, comprising:

an insulation film having a hollow at a top surface; and

a laminated body obtained by laminating a plurality of layers on said top surface and etching a region of said plurality of layers corresponding to a region other than said hollow, wherein said laminated body includes a lower electrode layer, a ferroelectric layer formed on said lower electrode layer and an upper electrode layer formed on said ferroelectric layer, and said lower electrode layer includes a first electrode portion formed at a corner of said hollow and a second electrode portion formed on said first electrode portion.

4. (Twice Amended) A ferroelectric memory, comprising:

an insulation film having a concave portion at a top surface; and

a laminated body obtained by laminating a plurality of layers on said top surface and etching a region of said plurality of layers corresponding to a region other than said concave portion, wherein said laminated body includes a lower electrode layer which is brought into contact with a bottom surface of said concave portion, thin film of a same